

# XR8051, XR8052, XR8054

# Low Cost, High Speed Rail-to-Rail Amplifiers

#### **FEATURES**

- 175MHz bandwidth
- Fully specified at +3V, +5V and +/-5V supplies
- Output voltage range: 0.03V to 4.95V;  $V_s = +5$ ;  $R_1 = 2k\Omega$
- Input voltage range:-0.3V to +4.1V; V<sub>s</sub> = +5
- 190V/µs slew rate
- 2.6mA supply current per amplifier
- ±100mA linear output current
- ±125mA short circuit current
- XR8051 directly replaces AD8051, AD8091
- XR8052 directly replaces AD8052, AD8092
- XR8054 directly replaces AD8054

#### **APPLICATIONS**

- Video driver
- Video surveillance and distributior
- A/D driver
- Active filters
- CCD imaging systems
- CD/DVD ROM
- Coaxial cable drivers
- High capacitive load driver
- Portable/battery-powered applications
- Twisted pair driver
- Telecom and optical terminals

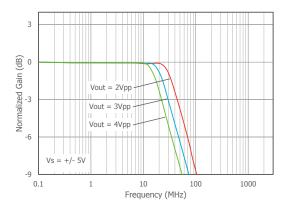
### **General Description**

The XR8051 (single), XR8052 (dual) and XR8054(quad) are low cost, voltage feedback amplifiers. These amplifiers are designed to operate on  $\pm 3V$  to  $\pm 5V$ , or  $\pm 5V$  supplies. The input voltage range extends  $\pm 300$  below the negative rail and  $\pm 0.9V$  below the positive rail.

The XR8051, XR8052, and XR8054 offer superior dynamic performance with a 175MHz small signal bandwidth and 190V/ $\mu$ s slew rate. The combination of low power, high output current drive, and rail-to-rail performance make these amplifiers well suited for battery-powered systems and video applications.

The combination of low cost and high performance make the XR8051, XR8052, and XR8054 suitable for high volume applications in both consumer and industrial applications such as video surveillance and distribution systems, professional and IPC cameras, active filter circuits, coaxial cable drivers, and electronic white boards.

## Large Signal Frequency Response at +/-5V

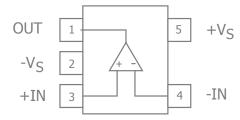


## Ordering Information

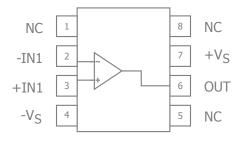
Part Number	Package	MSL Rating	Pb-Free	RoHS Compliant	Operating Temperature	Packaging Method
XR8051ASO8X	SOIC-8	MSL-2	Yes	Yes	-40°C to +125°C	Reel
XR8051AST5X	TSOT-5	MSL-1	Yes	Yes	-40°C to +125°C	Reel
XR8052ASO8X	SOIC-8	MSL-2	Yes	Yes	-40°C to +125°C	Reel
XR8052AMP8X	MSOP-8	MSL-1	Yes	Yes	-40°C to +125°C	Reel
XR8054ASO14X	SOIC-14	MSL-2	Yes	Yes	-40°C to +125°C	Reel
XR8054ATP14X	TSSOP-14	MSL-1	Yes	Yes	-40°C to +125°C	Reel

## XR8051 Pin Configurations

## TSOT-5

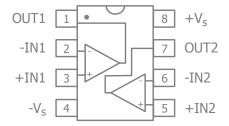


## SOIC-8



## XR8052 Pin Configuration

## SOIC-8 / MSOP-8



## XR8051 Pin Assignments

### TSOT-5

Pin No.	Pin Name	Description
1	OUT	Output
2	-V <sub>S</sub>	Negative supply
3	+IN	Positive input
4	-IN	Negative input
5	+V <sub>S</sub>	Positive supply

## SOIC-8

Pin No.	Pin Name	Description
1	NC	No Connect
2	-IN	Negative input
3	+IN	Positive input
4	-V <sub>S</sub>	Negative supply
5	NC	No Connect
6	OUT	Negative input
7	+V <sub>S</sub>	Positive supply
8	NC	No Connect

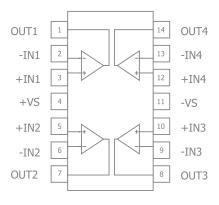
## XR8052 Pin Assignments

## SOIC-8 / MSOP-8

Pin No. Pin Name Description  OUT1 Output, channel 1  Positive input, channel 1  Positive input, channel 1  Vs Negative supply  Final Negative supply  Negative input, channel 2  Negative input, channel 2			
2 -IN1 Negative input, channel 1 3 +IN1 Positive input, channel 1 4 -V <sub>S</sub> Negative supply 5 +IN2 Positive input, channel 2 6 -IN2 Negative input, channel 2	Pin No.	Pin Name	Description
3 +IN1 Positive input, channel 1 4 -V <sub>S</sub> Negative supply 5 +IN2 Positive input, channel 2 6 -IN2 Negative input, channel 2	1	OUT1	Output, channel 1
4 -V <sub>S</sub> Negative supply 5 +IN2 Positive input, channel 2 6 -IN2 Negative input, channel 2	2	-IN1	Negative input, channel 1
5 +IN2 Positive input, channel 2 6 -IN2 Negative input, channel 2	3	+IN1	Positive input, channel 1
6 -IN2 Negative input, channel 2	4	-V <sub>S</sub>	Negative supply
the state of the s	5	+IN2	Positive input, channel 2
7 OUT? Output channel ?	6	-IN2	Negative input, channel 2
/ Outz Output, Channel 2	7	OUT2	Output, channel 2
8 +V <sub>S</sub> Positive supply	8	+V <sub>S</sub>	Positive supply

## XR8054 Pin Configuration

## SOIC/TSSOP



## XR8054 Pin Assignments

## SOIC/TSSOP

Pin No.	Pin Name	Description
1	OUT1	Output, channel 1
2	-IN1	Negative input, channel 1
3	+IN1	Positive input, channel 1
4	+V <sub>S</sub>	Positive supply
5	+IN2	Positive input, channel 2
6	-IN2	Negative input, channel 2
7	OUT2	Output, channel 2
8	OUT3	Output, channel 3
9	-IN3	Negative input, channel 3
10	+IN3	Positive input, channel 3
11	-V <sub>S</sub>	Negative supply
12	+IN4	Positive input, channel 4
13	-IN4	Negative input, channel 4
14	OUT4	Output, channel 4

### **Absolute Maximum Ratings**

The safety of the device is not guaranteed when it is operated above the "Absolute Maximum Ratings". The device should not be operated at these "absolute" limits. Adhere to the "Recommended Operating Conditions" for proper device function. The information contained in the Electrical Characteristics tables and Typical Performance plots reflect the operating conditions noted on the tables and plots.

Parameter	Min	Max	Unit
Supply Voltage	0	+14	V
Input Voltage Range	-V <sub>S</sub> -0.5V	+V <sub>S</sub> +0.5V	V

### **Reliability Information**

Parameter	Min	Тур	Max	Unit
Junction Temperature			150	°C
Storage Temperature Range	-65		170	°C
Lead Temperature (Soldering, 10s)			260	°C
Package Thermal Resistance				
5-Lead SOT23		221		°C/W
8-Lead MSOP		139		°C/W
8-Lead SOIC		100		°C/W
14-Lead SOIC		88		°C/W
14-Lead TSSOP		96		°C/W

Notes:

Package thermal resistance ( $\theta_{\text{JA}}$ ), JDEC standard, multi-layer test boards, still air.

#### **ESD Protection**

Product	SOIC-8
Human Body Model (HBM)	1k
Charged Device Model (CDM)	2k

## **Recommended Operating Conditions**

Parameter	Min	Тур	Max	Unit
Operating Temperature Range	-40		+125	°C
Supply Voltage Range	2.7		12.6	V

## Electrical Characteristics at +3V

 $T_A=25^{\circ}\text{C},\,R_f=1.5k\Omega,\,R_L=2k\Omega$  to  $V_\text{S}/2,\,G=2;$  unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Frequency I	Domain Response		,			
GBWP	-3dB Gain Bandwidth Product	$G = +11, V_{OUT} = 0.2V_{pp}$		62		MHz
UGBW	Unity Gain Bandwidth	$V_{OUT} = 0.2V_{pp}, R_F = 0$		160		MHz
BW <sub>SS</sub>	-3dB Bandwidth	V <sub>OUT</sub> = 0.2V <sub>pp</sub>		60		MHz
f <sub>0.1dB</sub>	0.1dB gain flatness	$V_{OUT} = 0.2V_{pp}, R_L = 150\Omega$		20		MHz
BW <sub>LS</sub>	Large Signal Bandwidth	$V_{OUT} = 2V_{pp}$		40		MHz
DG	Differential Gain	DC-coupled Ouput		0.03		%
		AC-coupled Ouput		0.04		%
DP	Differential Phase	DC-coupled Ouput		0.03		0
		AC-coupled Ouput		0.06		0
Time Doma	in Response					'
t <sub>R</sub> , t <sub>F</sub>	Rise and Fall Time	V <sub>OUT</sub> = 0.2V step; (10% to 90%)		5		ns
$t_S$	Settling Time to 0.1%	V <sub>OUT</sub> = 1V step		25		ns
OS	Overshoot	V <sub>OUT</sub> = 0.2V step		8		%
SR	Slew Rate	G=-1, 2V step		165		V/µs
Distortion/N	loise Response					
THD	Total Harmonic Distortion	1MHz, Vout=1Vpp		75		dBc
e <sub>n</sub>	Input Voltage Noise	> 50kHz		16		nV/√Hz
X <sub>TALK</sub>	Crosstalk	f=5MHz		58		dB
DC Perform	ance	,		'		
V <sub>IO</sub>	Input Offset Voltage			0.5		mV
dV <sub>IO</sub>	Average Drift			5		μV/°C
$I_b$	Input Bias Current			1.4		μΑ
dI <sub>b</sub>	Average Drift			2		nA/°C
I <sub>os</sub>	Input Offset Current			0.05		μΑ
PSRR	Power Supply Rejection Ratio	DC		102		dB
A <sub>OL</sub>	Open-Loop Gain	$R_L = 2k\Omega^{(2)}$		92		dB
$I_{S}$	Supply Current	per channel		2.6		mA
Input Chara	cteristics					,
C <sub>IN</sub>	Input Capacitance			0.5		pF
CMIR	Common Mode Input Range			-0.3 to 2.1		V
CMRR	Common Mode Rejection Ratio	DC , V <sub>cm</sub> =0V to 1.5V		100		dB
Output Cha		- / till				
- a a p a a a a a a		$R_L = 150\Omega$		0.2+-		
		13012		0.3 to 2.75		V
V <sub>OUT</sub>	Output Voltage Swing	$R_L = 2k\Omega$		0.02 to 2.96		V
I <sub>OUT</sub>	Output Current			±100		mA
I <sub>SC</sub>	Short-Circuit Output Current	$V_{OUT} = V_S / 2$		±125		mA
V <sub>S</sub>	Power Supply Operationg Range	301		2.7 to 12		V

#### Notes:

- 1. 100% tested at 25°C
- 2. Guranteed by characterization, simulation or statistical anlysis

## Electrical Characteristics at +5V

 $T_A=25^{\circ}\text{C},\,R_f=1.5k\Omega,\,R_L=2k\Omega$  to  $V_\text{S}/2,\,G=2;$  unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Frequency [	Domain Response	<u> </u>				
GBWP	-3dB Gain Bandwidth Product	$G = +11, V_{OUT} = 0.2V_{pp}$		64		MHz
UGBW	Unity Gain Bandwidth	$V_{OUT} = 0.2V_{pp}, R_F = 0$		165		MHz
BW <sub>SS</sub>	-3dB Bandwidth	$V_{OUT} = 0.2V_{pp}$		62		MHz
f <sub>0.1dB</sub>	0.1dB gain flatness	$V_{OUT} = 0.2V_{pp}, R_L = 150\Omega$		20		MHz
BW <sub>LS</sub>	Large Signal Bandwidth	$V_{OUT} = 2V_{pp}$		45		MHz
DG	Differential Gain	DC-coupled Ouput		0.03		%
		AC-coupled Ouput		0.04		%
DP	Differential Phase	DC-coupled Ouput		0.03		0
		AC-coupled Ouput		0.06		0
Time Doma	in Response		<b>'</b>			1
t <sub>R</sub> , t <sub>F</sub>	Rise and Fall Time	V <sub>OUT</sub> = 0.2V step		5		ns
t <sub>S</sub>	Settling Time to 0.1%	V <sub>OUT</sub> = 2V step		25		ns
OS	Overshoot	V <sub>OUT</sub> = 0.2V step		5		%
SR	Slew Rate	G=-1 , 4V step,		185		V/µs
Distortion/N	loise Response		'			
THD	Total Harmonic Distortion	1MHz, V <sub>OUT</sub> =2V <sub>PP</sub>		-75		dB
e <sub>n</sub>	Input Voltage Noise	> 50kHz		16		nV/√Hz
X <sub>TALK</sub>	Crosstalk	f=5MHz		58		dB
DC Perform	ance		<u>'</u>			
V <sub>IO</sub>	Input Offset Voltage(1)		-7	0.5	7	mV
dV <sub>IO</sub>	Average Drift			5		μV/°C
$I_b$	Input Bias Current (1)		-2	1.4	2	μΑ
dI <sub>b</sub>	Average Drift			2		nA/°C
I <sub>os</sub>	Input Offset Current (1)		-0.75	0.05	0.75	μΑ
PSRR	Power Supply Rejection Ratio (1)	DC	80	102		dB
A <sub>OL</sub>	Open-Loop Gain	$R_L = 2k\Omega^{(2)}$	80	92		dB
$I_S$	Supply Current (1)	per channel		2.6	4	mA
Input Chara	acteristics	,	'			
C <sub>IN</sub>	Input Capacitance			0.5		pF
CMIR	Common Mode Input Range			-0.3 to 4.1		V
CMDD	Common Mode Poinstian Patia (1)	DC V = 0V to 2 EV	75			dD
CMRR	Common Mode Rejection Ratio (1)	DC , V <sub>cm</sub> = 0V to 3.5V	75	100		dB
Output Cha	racteristics					T
V	Output Voltago Swing	$R_L = 150\Omega^{(1)}$	4.65	0.1 to 4.9	0.35	V
V <sub>OUT</sub>	Output Voltage Swing	$R_L = 2k\Omega$		0.03 to 4.95		V
$I_{OUT}$	Output Current			±100		mA
$I_{SC}$	Short-Circuit Output Current	$V_{OUT} = V_S / 2$		±125		mA
V <sub>S</sub>	Power Supply Operationg Range			2.7 to 12		V

#### Notes:

- 1. 100% tested at 25°C
- 2. Guranteed by characterization, simulation or statistical anlysis

### Electrical Characteristics at ±5V

 $T_A=25^{\circ}\text{C},\,R_f=1.5\text{k}\Omega,\,R_L=2\text{k}\Omega$  to GND, G=2; unless otherwise noted.

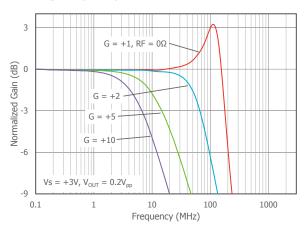
Symbol	Parameter	Conditions	Min	Тур	Max	Units
Frequency D	Domain Response	'				
GBWP	-3dB Gain Bandwidth Product	$G = +11, V_{OUT} = 0.2V_{pp}$		65		MHz
UGBW	Unity Gain Bandwidth	$V_{OUT} = 0.2V_{pp}, R_F = 0$		175		MHz
BW <sub>SS</sub>	-3dB Bandwidth	$V_{OUT} = 0.2V_{pp}$		65		MHz
f <sub>0.1dB</sub>	0.1dB gain flatness	$V_{OUT} = 0.2V_{pp}, R_L = 150\Omega$		20		MHz
BW <sub>LS</sub>	Large Signal Bandwidth	$V_{OUT} = 2V_{pp}$		50		MHz
DG	Differential Gain	DC-coupled Ouput		0.03		%
		AC-coupled Ouput		0.04		%
DP	Differential Phase	DC-coupled Ouput		0.03		0
		AC-coupled Ouput		0.06		0
Time Domai	n Response					
t <sub>R</sub> , t <sub>F</sub>	Rise and Fall Time	V <sub>OUT</sub> = 0.2V step		5		ns
t <sub>S</sub>	Settling Time to 0.1%	$V_{OUT} = 2V$ step, $R_L = 100\Omega$		25		ns
OS	Overshoot	V <sub>OUT</sub> = 0.2V step		5		%
SR	Slew Rate	G=-1, 5V step		190		V/µs
Distortion/N	loise Response		'			
THD	Total Harmonic Distortion	1MHz, V <sub>OUT</sub> =2V <sub>PP</sub>		76		dBc
e <sub>n</sub>	Input Voltage Noise	> 50kHz		16		nV/√Hz
X <sub>TALK</sub>	Crosstalk	f=5MHz		58		dB
DC Performa	ance	'				'
V <sub>IO</sub>	Input Offset Voltage			0.5		mV
dV <sub>IO</sub>	Average Drift			5		μV/°C
I <sub>b</sub>	Input Bias Current			1.3		μΑ
dI <sub>b</sub>	Average Drift			2		nA/°C
I <sub>os</sub>	Input Offset Current			0.04		μΑ
PSRR	Power Supply Rejection Ratio	DC		102		dB
A <sub>OL</sub>	Open-Loop Gain	$R_L = 2k\Omega^{(2)}$		92		dB
I <sub>S</sub>	Supply Current	per channel		2.6		mA
Input Chara	cteristics	'				'
C <sub>IN</sub>	Input Capacitance			0.5		pF
CMIR	Common Mode Input Range			-5.3 to 4.1		V
CMDD	Common Mode Pointing Potic (1)	DC V				40
CMRR	Common Mode Rejection Ratio (1)	DC , V <sub>cm</sub> = -5V to 3.5V		100		dB
Output Char	acteristics					1
V	Output Voltage Swing	$R_L = 150\Omega$		-4.8 to 4.8		V
V <sub>OUT</sub>	Output voitage Swing	$R_L = 2k\Omega$		-4.95 to 4.93		V
I <sub>OUT</sub>	Output Current			+/ -100		mA
I <sub>SC</sub>	Short-Circuit Output Current	$V_{OUT} = V_S / 2$		+/-125		mA
V <sub>S</sub>	Power Supply Operationg Range			2.7 to 12		V

#### Notes:

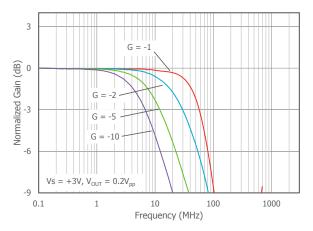
- 1. 100% tested at 25°C
- 2. Guranteed by characterization, simulation or statistical anlysis

TA = 25°C,  $V_S$  = +3V,  $R_L$  = 2k $\Omega$  to  $V_S/2$ ,  $A_V$ =+2,  $R_F$ =1.5k $\Omega$ ; unless otherwise noted.

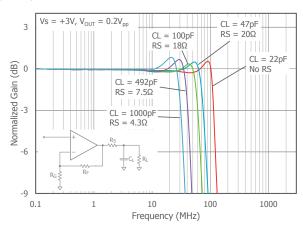
### Non-Inverting Freq. Resp.



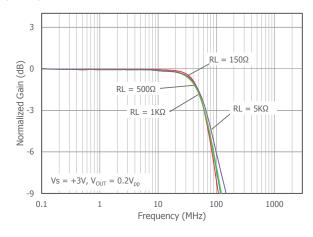
### Inverting Freq. Resp.



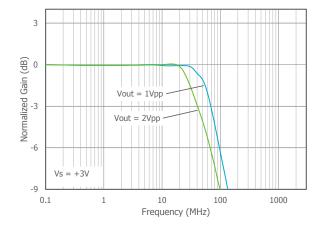
Freq. Resp. vs CL



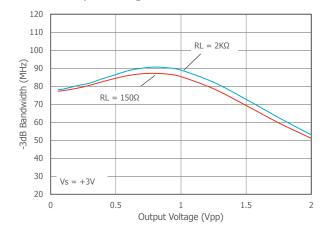
Freq. Resp. vs RL



Large Signal Freq. Resp.

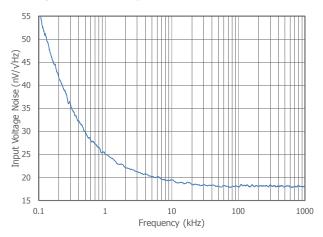


-3db BW vs Output Voltage

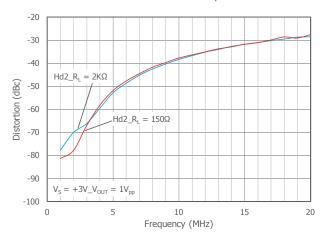


TA = 25°C,  $V_S$  = +3V,  $R_L$  = 2k $\Omega$  to  $V_S/2$ ,  $A_V$ =+2,  $R_F$ =1.5k $\Omega$  ; unless otherwise noted.

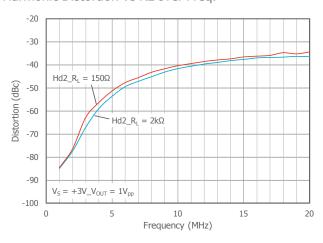
Input Voltage Noise vs Freq.



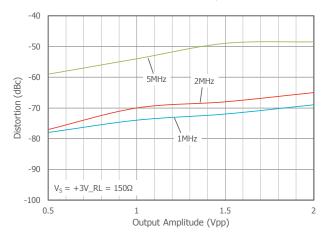
2nd Harmonic Distortion Vs RL over Freq.



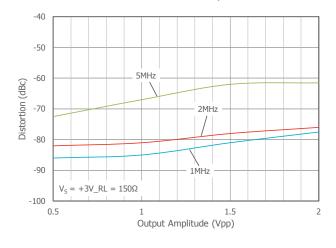
3rd Harmonic Distortion Vs RL over Freq.



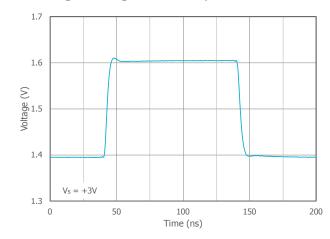
2nd Harmonic Distortion Vs Vo over Freq.



3rd Harmonic Distortion Vs Vo over Freq.

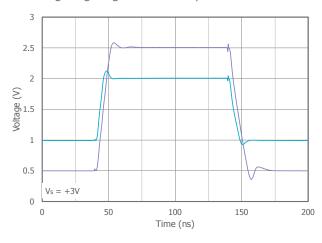


Non-Inverting Small Signal Pulse Response

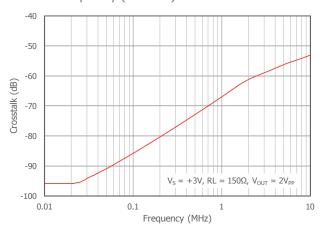


TA = 25°C,  $V_S$  = +3V,  $R_L$  = 2k $\Omega$  to  $V_S/2$ ,  $A_V$ =+2,  $R_F$ =1.5k $\Omega$ ; unless otherwise noted.

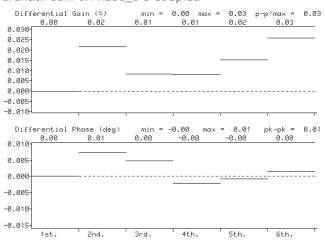
### Non-Inverting Large Signal Pulse Response



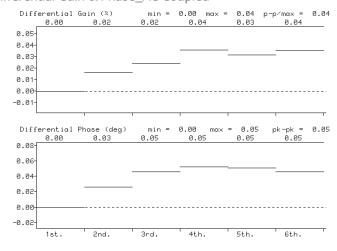
### Crosstalk vs Frequency (XR8052)



#### Differential Gain & Phase\_DC Coupled

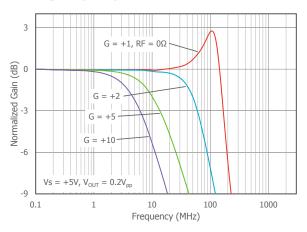


#### Differential Gain & Phase\_AC Coupled

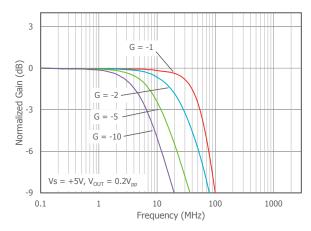


TA = 25°C,  $V_S$  = +5V,  $R_L$  = 2k $\Omega$  to  $V_S/2$ ,  $A_V$ =+2,  $R_F$ =1.5k $\Omega$ ; unless otherwise noted.

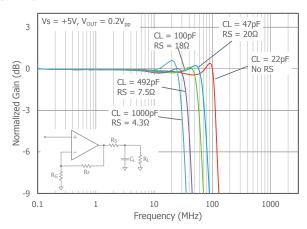
### Non-Inverting Freq. Resp.



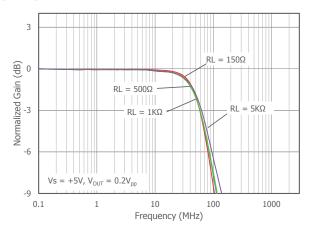
### Inverting Freq. Resp.



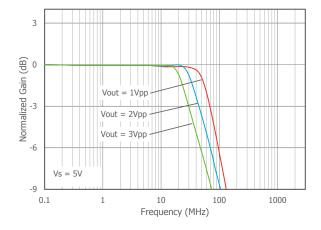
Freq. Resp. vs CL



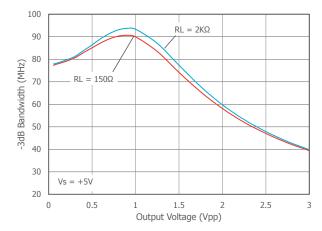
Freq. Resp. vs RL



Large Signal Freq. Resp.

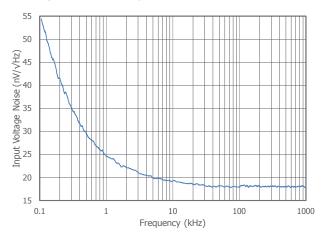


-3db BW vs Output Voltage

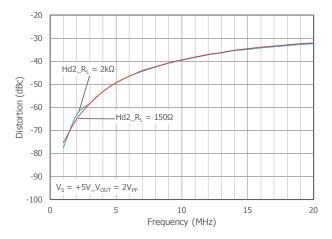


TA = 25°C,  $V_S$  = +5V,  $R_L$  = 2k $\Omega$  to  $V_S/2$ ,  $A_V$ =+2,  $R_F$ =1.5k $\Omega$  ; unless otherwise noted.

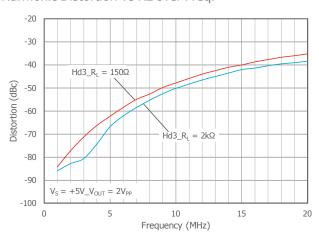
Input Voltage Noise vs Freq.



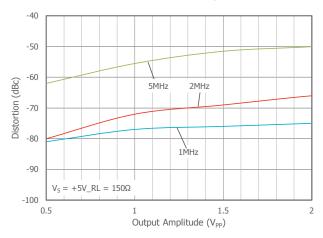
2nd Harmonic Distortion Vs RL over Freq.



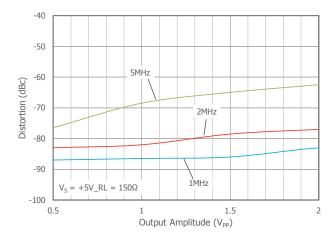
3rd Harmonic Distortion Vs RL over Freq.



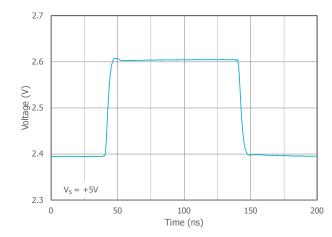
2nd Harmonic Distortion Vs Vo over Freq.



3rd Harmonic Distortion Vs Vo over Freq.

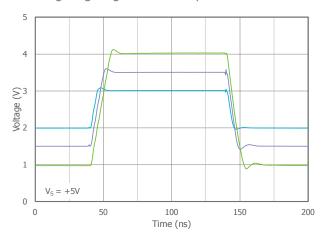


Non-Inverting Small Signal Pulse Response

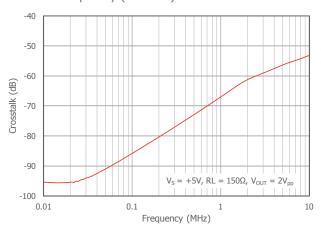


TA = 25°C,  $V_S$  = +5V,  $R_L$  = 2k $\Omega$  to  $V_S/2$ ,  $A_V$ =+2,  $R_F$ =1.5k $\Omega$ ; unless otherwise noted.

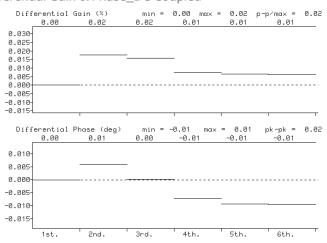
### Non-Inverting Large Signal Pulse Response



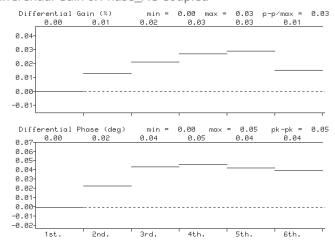
### Crosstalk vs Frequency (XR8052)



#### Differential Gain & Phase\_DC Coupled

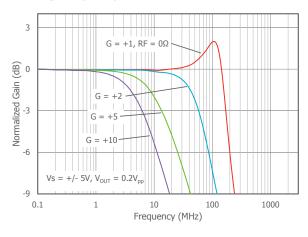


#### Differential Gain & Phase\_AC Coupled

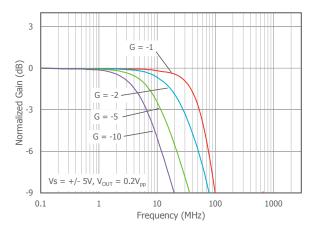


TA = 25°C,  $V_S = \pm 5V$ ,  $R_L = 2k\Omega$  to GND,  $A_V = +2$ ,  $R_F = 1.5k\Omega$ ; unless otherwise noted.

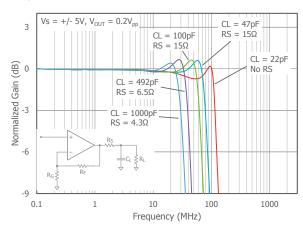
### Non-Inverting Freq. Resp.



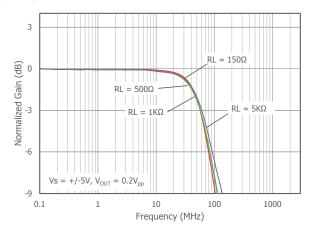
### Inverting Freq. Resp.



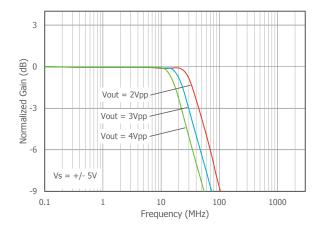
Freq. Resp. vs CL



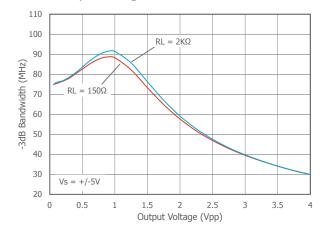
Freq. Resp. vs RL



Large Signal Freq. Resp.

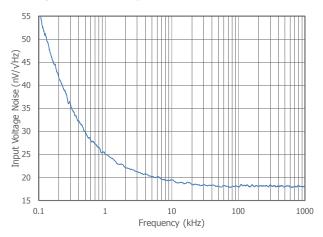


-3db BW vs Output Voltage

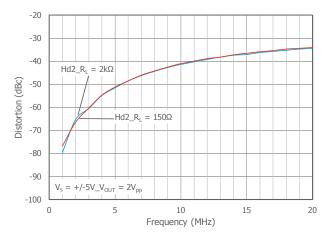


TA = 25°C,  $V_S = \pm 5V$ ,  $R_L = 2k\Omega$  to GND,  $A_V = +2$ ,  $R_F = 1.5k\Omega$ ; unless otherwise noted.

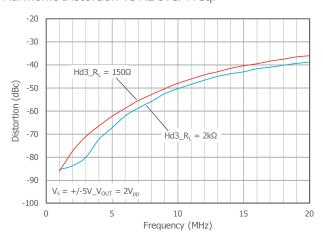
Input Voltage Noise vs Freq.



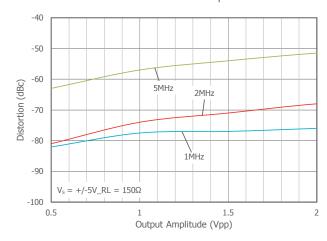
2nd Harmonic Distortion Vs RL over Freq.



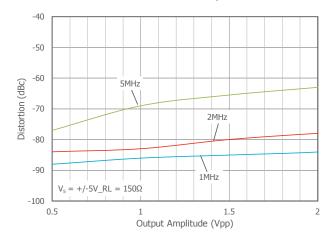
3rd Harmonic Distortion Vs RL over Freq.



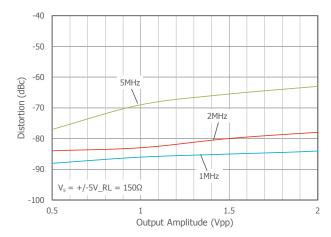
2nd Harmonic Distortion Vs Vo over Freq.



3rd Harmonic Distortion Vs Vo over Freq.

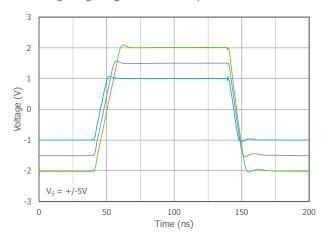


Non-Inverting Small Signal Pulse Response

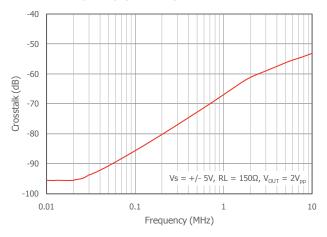


TA = 25°C,  $V_S = \pm 5V$ ,  $R_L = 2k\Omega$  to GND,  $A_V = +2$ ,  $R_F = 1.5k\Omega$ ; unless otherwise noted.

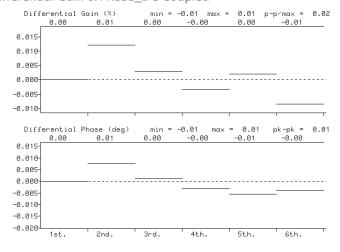
### Non-Inverting Large Signal Pulse Response



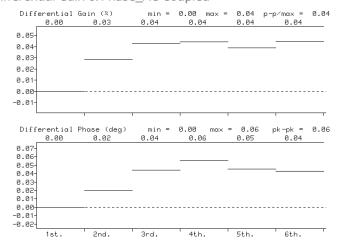
### Crosstalk vs Frequency (XR8052)



### Differential Gain & Phase\_DC Coupled



#### Differential Gain & Phase\_AC Coupled



### **Application Information**

#### General Description

The XR8051, XR8052, and XR8054 are single supply, general purpose, voltage-feedback amplifiers fabricated on a complementary bipolar process using a patent pending topography. They feature a rail-to-rail output stage and is unity gain stable.

The common mode input range extends to 300mV below ground and to 0.9V below  $V_{\rm S}$ . Exceeding these values will not cause phase reversal. However, if the input voltage exceeds the rails by more than 0.5V, the input ESD devices will begin to conduct. The output will stay at the rail during this overdrive condition.

The output stage is short circuit protected and offers "soft" saturation protection that improves recovery time.

Figures 1, 2, and 3 illustrate typical circuit configurations for non-inverting, inverting, and unity gain topologies for dual supply applications. They show the recommended bypass capacitor values and overall closed loop gain equations. Figure 4 shows the typical non-inverting gain circuit for single supply applications.

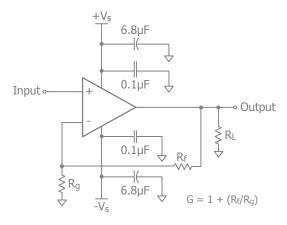


Figure 1. Typical Non-Inverting Gain Circuit

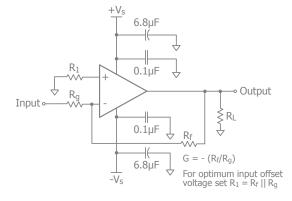


Figure 2. Typical Inverting Gain Circuit

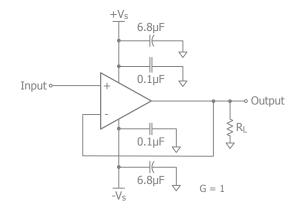


Figure 3. Unity Gain Circuit

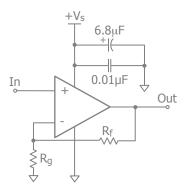


Figure 4. Single Supply Non-Inverting Gain Circuit

#### Overdrive Recovery

For an amplifier, an overdrive condition occurs when the output and/or input ranges are exceeded. The recovery time varies based on whether the input or output is overdriven and by how much the ranges are exceeded. The XR8051, XR8052, and XR8054 will typically recover in less than 20ns from an overdrive condition. Figure 5 shows the XR8052 in an overdriven condition.

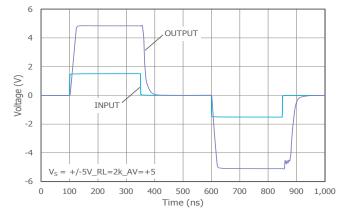


Figure 5: Overdrive Recovery

### **Power Dissipation**

Power dissipation should not be a factor when operating under the stated  $2k\Omega$  load condition. However, applications with low impedance, DC coupled loads should be analyzed to ensure that maximum allowed junction temperature is not exceeded. Guidelines listed below can be used to verify that the particular application will not cause the device to operate beyond it's intended operating range.

Maximum power levels are set by the absolute maximum junction rating of 170°C. To calculate the junction temperature, the package thermal resistance value Theta<sub>JA</sub> ( $\Theta_{JA}$ ) is used along with the total die power dissipation.

$$T_{Junction} = T_{Ambient} + (\Theta_{JA} \times P_{D})$$

Where T<sub>Ambient</sub> is the temperature of the working environment.

In order to determine  $P_D$ , the power dissipated in the load needs to be subtracted from the total power delivered by the supplies.

$$P_D = P_{supply} - P_{load}$$

Supply power is calculated by the standard power equation.

$$P_{supply} = V_{supply} \times I_{RMS supply}$$
  
 $V_{supply} = V_{S+} - V_{S-}$ 

Power delivered to a purely resistive load is:

$$P_{load} = ((V_{LOAD})_{RMS^2})/Rload_{eff}$$

The effective load resistor (Rload<sub>eff</sub>) will need to include the effect of the feedback network. For instance,

Rloadeff in Figure 3 would be calculated as:

$$R_{l} \mid \mid (R_{f} + R_{o})$$

These measurements are basic and are relatively easy to perform with standard lab equipment. For design purposes however, prior knowledge of actual signal levels and load impedance is needed to determine the dissipated power. Here,  $P_{\rm D}$  can be found from

$$P_D = P_{Quiescent} + P_{Dynamic} - P_{Load}$$

Quiescent power can be derived from the specified  $I_S$  values along with known supply voltage,  $V_{Supply}$ . Load power can be calculated as above with the desired signal

amplitudes using:

$$(V_{IOAD})_{RMS} = V_{PEAK} / \sqrt{2}$$

$$(I_{LOAD})_{RMS} = (V_{LOAD})_{RMS} / Rload_{eff}$$

The dynamic power is focused primarily within the output stage driving the load. This value can be calculated as:

$$P_{DYNAMIC} = (V_{S+} - V_{LOAD})_{RMS} \times (I_{LOAD})_{RMS}$$

Assuming the load is referenced in the middle of the power rails or  $V_{\text{supply}}/2$ .

The XR8051 is short circuit protected. However, this may not guarantee that the maximum junction temperature (+170°C) is not exceeded under all conditions. Figure 6 shows the maximum safe power dissipation in the package vs. the ambient temperature for the packages available.

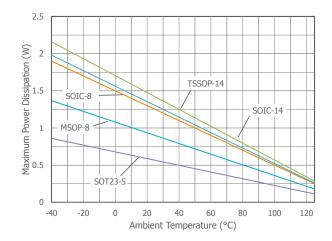


Figure 6. Maximum Power Derating

#### **Driving Capacitive Loads**

Increased phase delay at the output due to capacitive loading can cause ringing, peaking in the frequency response, and possible unstable behavior. Use a series resistance, R<sub>S</sub>, between the amplifier and the load to help improve stability and settling performance. Refer to Figure 7.

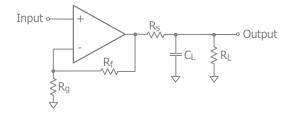


Figure 7. Addition of R<sub>S</sub> for Driving Capacitive Loads

Table 1 provides the recommended  $R_S$  for various capacitive loads. The recommended  $R_S$  values result in approximately <1dB peaking in the frequency response.

CL (Pf)	Rs (Ω)	-3db BW (MHz)
22pF	0	120
47pF	15	80
100pF	15	65
492pF	6.5	40

Table 1: Recommended R<sub>S</sub> vs. C<sub>I</sub>

For a given load capacitance, adjust  $R_S$  to optimize the tradeoff between settling time and bandwidth. In general, reducing  $R_S$  will increase bandwidth at the expense of additional overshoot and ringing.

#### **Layout Considerations**

General layout and supply bypassing play major roles in high frequency performance. CADEKA has evaluation boards to use as a guide for high frequency layout and as an aid in device testing and characterization. Follow the steps below as a basis for high frequency layout:

- Include 6.8µF and 0.1µF ceramic capacitors for power supply decoupling
- Place the 6.8µF capacitor within 0.75 inches of the power pin
- Place the 0.1µF capacitor within 0.1 inches of the power pin
- Remove the ground plane under and around the part, especially near the input and output pins to reduce parasitic capacitance
- Minimize all trace lengths to reduce series inductances

Refer to the evaluation board layouts below for more information.

#### **Evaluation Board Information**

The following evaluation boards are available to aid in the testing and layout of these devices:

Evaluation Board	Products	
CEB002	XR8051 in SOT23	
CEB003	XR8051 in SOIC	

Evaluation Board	Products	
CEB006	XR8052 in SOIC	
CEB010	XR8052 in MSOP	
CEB018	XR8054 in SOIC	

#### **Evaluation Board Schematics**

Evaluation board schematics and layouts are shown in Figures 10-18. These evaluation boards are built for dual-supply operation. Follow these steps to use the board in a single-supply application:

- 1. Short -Vs to ground.
- 2. Use C3 and C4, if the -V<sub>S</sub> pin of the amplifier is not directly connected to the ground plane.

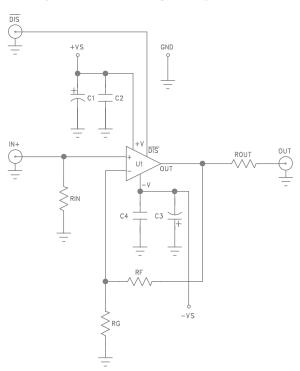


Figure 8. CEB002 & CEB003 Schematic

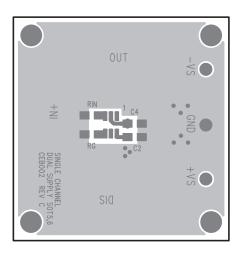


Figure 9. CEB002 Top View

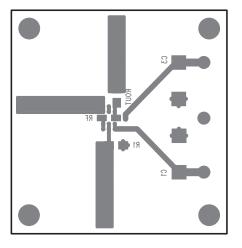


Figure 10. CEB002 Bottom View

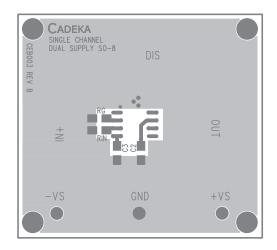


Figure 11. CEB003 Top View

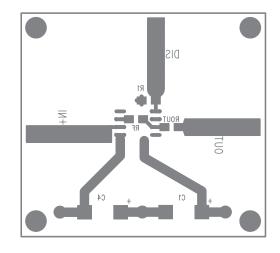


Figure 12. CEB003 Bottom View

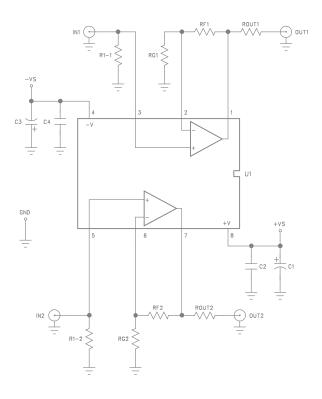


Figure 13. CEB006 & CEB010 Schematic

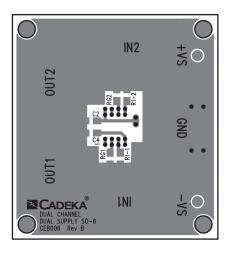


Figure 14. CEB006 Top View

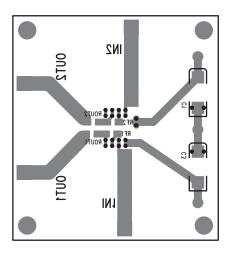


Figure 15. CEB006 Bottom View

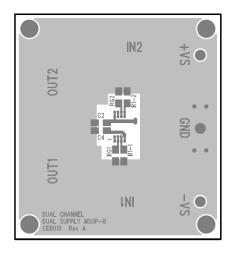


Figure 16. CEB010 Top View

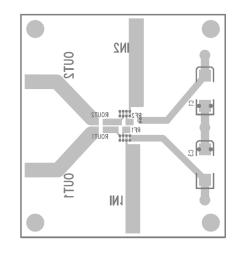


Figure 17. CEB010 Bottom View

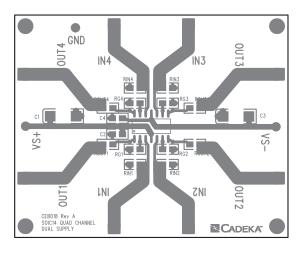


Figure 19. CEB018 Bottom View

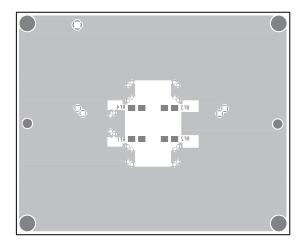
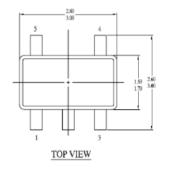


Figure 20. CEB018 Bottom View

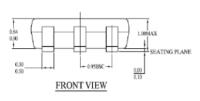
## **Mechanical Dimensions**

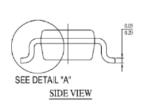
### TSOT-5 Package

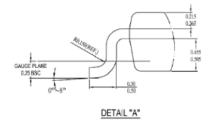


#### NOTE:

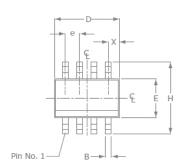
- 1. ALL DIMENSIONS ARE IN MILLIMETERS.
- 2. PACKAGE LENGTH DOES NOT INCLUDE INTERLEAD FALSH OR PROTRUSION
- 3. PACKAGE WIDTH DOES NOTINCLUDE INTERLEAD FALSH OR PROTRUSION.
- LEAD COPLANARITY (BOTTOM OF LEADS AFTER FORMING) SHALL BE 0.10 MILLIMETERS MAX.
- 5. DRAWING CONFROMS TO JEDEC MO-193, VARIATION AA.
- 6. DRAWING IS NOT TO SCALE.



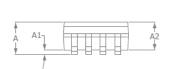


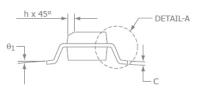


SOIC-8









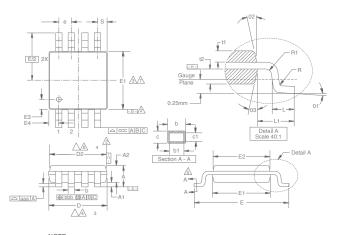
SOIC-8		
SYMBOL	MIN	MAX
A1	0.10	0.25
В	0.36	0.48
С	0.19	0.25
D	4.80	4.98
Е	3.81	3.99
е	1.27 BSC	
Н	5.80	6.20
h	0.25	0.5
L	0.41	1.27
Α	1.37	1.73
$\theta_1$	00	8°
Х	0.55	ref
θ <sub>2</sub>	7°	BSC

#### NOTE:

- 1. All dimensions are in millimeters.
- 2. Lead coplanarity should be 0 to 0.1mm (0.004") max.
- 3. Package surface finishing: VDI 24~27
- 4. All dimension excluding mold flashes.
- The lead width, B to be determined at 0.1905mm from the lead tip.

#### Mechanical Dimensions continued

#### MSOP-8

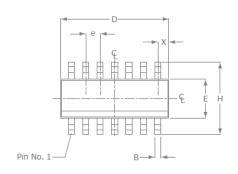


		Max
Symbol	Min	Max
A	1.10	-
A1	0.10	±0.05
A2	0.86	±0.08
D	3.00	±0.10
D2	2.95	±0.10
E	4.90	±0.15
E1	3.00	±0.10
E2	2.95	±0.10
E3	0.51	±0.13
E4	0.51	±0.13
R	0.15	+0.15/-0.06
R1	0.15	+0.15/-0.06
t1	0.31	±0.08
t2	0.41	±0.08
b	0.33	+0.07/-0.08
b1	0.30	±0.05
С	0.18	±0.05
c1	0.15	+0.03/-0.02
01	3.0°	±3.0°
02	12.0°	±3.0°
03	12.0°	±3.0°
L	0.55	±0.15
L1	0.95 BSC	-
aaa	0.10	-
bbb	0.08	-
ccc	0.25	-
е	0.65 BSC	-
S	0.525 BSC	-

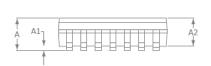
#### NOTE:

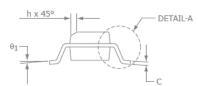
- ns are in millimeters (angle in degrees), unless otherwise specific 1 All dimer
- A Dimensions "D" and "E1" are to be determined at datum FH-I.
- Dimensions "D2" and "E2" are for top package and dimensions "D" and "E1" are for bottom package
- ⚠ Cross sections A A to be determined at 0.13 to 0.25mm from the leadtip
- A Dimension "D" and "D2" does not include mold flash, protrusion or gate burrs
- Dimension "E1" and "E2" does not include interlead flash or protrusion

#### SOIC-14 Package









	SOIC-14	
SYMBOL	MIN	MAX
A1	0.10	0.25
В	0.36	0.48
С	0.19	0.25
D	8.56	8.74
Е	3.84	3.99
е	1.27 BSC	
Н	5.80	6.20
h	0.25	0.5
L	0.41	1.27
Α	1.37	1.73
$\theta_1$	0°	80
Х	0.51 ref	
$\theta_2$	7º BSC	

#### NOTE:

- 1. All dimensions are in millimeters.
- 2. Lead coplanarity should be 0 to 0.1mm (0.004") ma
- 3. Package surface finishing: VDI 24~27
- 4. All dimension excluding mold flashes.
- 5. The lead width, B to be determined at 0.1905mm from the lead tip.

#### For Further Assistance:

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